

	Type	L #	Hits	Search Text	DBs
1	IS&R	L1	56	(257/922).CCLS.	USPAT
2	BRS	L2	1942	organic adj semiconductor	USPAT
3	BRS	L3	1	2 and tamper	USPAT
4	BRS	L4	7542	organic adj semiconductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB
5	BRS	L5	9	4 and tamper	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB
6	BRS	L6	634	4 and protection	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB
7	BRS	L7	2	4 and (protection adj portion)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB
8	BRS	L8	215	4 and crack	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB
9	BRS	L9	71	8 and memory	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB
10	BRS	L10	5	4 and (seal with strip\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Type	L #	Hits	Search Text	DBs
11	BRS	L11	6	4 and (protection with activat\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB